

# GD54/74HC58, GD54/74HCT58

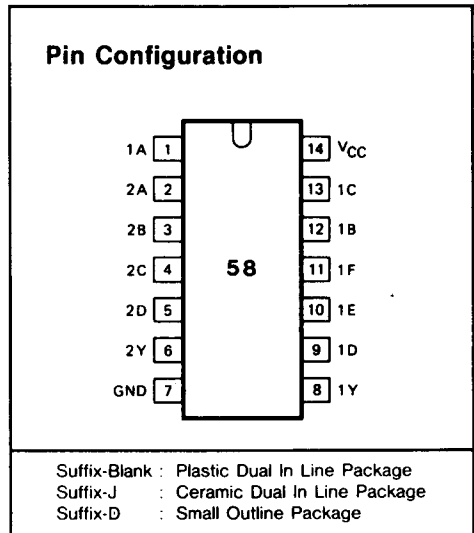
## DUAL AND-OR GATES

### General Description

These devices are identical in pinout to the 54/74LS58. They contain one 2-wide 2-input & one 2-wide 3-input AND-OR gates. These devices are characterized for operation over wide temperature ranges to meet industry and military specifications.

### Features

- Low Power consumption characteristic of CMOS devices
- Output drive capability: 10 LS TTL Loads Min.
- Operating speed superior to LS TTL
- Wide operating voltage range: for HC 2 to 6 volts  
for HCT 4.5 to 5.5 volts
- Low input current:  $1\mu\text{A}$  Max.
- Low quiescent current:  $20\mu\text{A}$  Max. (74HC)
- High noise immunity characteristic of CMOS
- Diode protection on all inputs.



### Logic Symbol

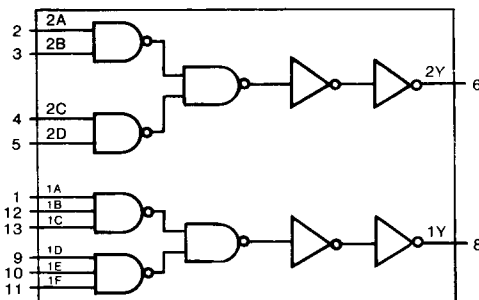


Fig. 1 Logic Symbol

### Function Table

INPUTS		OUTPUT
N*	M*	nY
L	L	L
H	L	H
L	H	H
H	H	H

$N^* = 1A \cdot 1B \cdot 1C$  or  $2A \cdot 2B$   
 $M^* = 1D \cdot 1E \cdot 1F$  or  $2C \cdot 2D$   
 $1Y = 1A \cdot 1B \cdot 1C + 1D \cdot 1E \cdot 1F$   
 $2Y = 2A \cdot 2B + 2C \cdot 2D$

**Absolute Maximum Ratings**

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CC}$	DC Supply voltage		-0.5	+7	V
$I_{IK}, I_{OK}$	DC input or output diode current	for $V_I < -0.5$ or $V_I > V_{CC} + 0.5V$		20	mA
$I_O$	DC output source or sink current	for $-0.5V < V_O < V_{CC} + 0.5V$		25	mA
$I_{CC}$	DC $V_{CC}$ or GND current			50	mA
$T_{stg}$	Storage temperature range		-65	150	°C
$P_D$	Power dissipation per package	above +70°C: derate linearly with 8mW/K		500	mW
$T_L$	Lead temperature	At distance 1/16 ± 1/32 in. from case for 60 sec(CERAMIC) 10 sec(PLASTIC)		300 260	°C

**Recommended Operating Conditions**

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range $V_{CC}$ : GD54/74HC Types GD54/74HCT Types	2 4.5	6 5.5	V
DC Input or Output Voltage $V_I, V_O$	0	$V_{CC}$	V
Operating Temperature $T_A$ : GD74 Types GD54 Types	-40 -55	+85 +125	°C
Input Rise and Fall times $t_r, t_f$ : GD54/74HC Types at 2V at 4.5V at 6V GD54/74HCT Types at 4.5V		1000 500 400 500	ns

DC Electrical Characteristics for HC

SYMBOL	PARAMETER	TEST CONDITION	V <sub>CC</sub> (V)	T <sub>A</sub> =25°C			GD74HC58		GD54HC58		UNIT	
				MIN.	TYP.	MAX.	MIN.	MAX.	MIN.	MAX.		
V <sub>IH</sub>	HIGH level input Voltage		2.0	1.5			1.5		1.5		V	
			4.5	3.15		3.15		3.15				
			6.0	4.2		4.2		4.2				
V <sub>IL</sub>	LOW level input voltage		2.0							0.3	V	
			4.5			0.3		0.3		0.9		
			6.0			0.9		1.2		1.2		
V <sub>OH</sub>	HIGH level output voltage	V <sub>IN</sub> =V <sub>IH</sub>	I <sub>OH</sub> =-20μA	2.0	1.9	2.0		1.9		1.9		V
				4.5	4.4	4.5		4.4		4.4		
				6.0	5.9	6.0		5.9		5.9		
		or V <sub>IL</sub>	I <sub>OH</sub> =-4mA I <sub>OH</sub> =-5.2mA	4.5	3.98	4.3		3.84		3.7		
				6.0	5.48	5.2		5.34		5.2		
V <sub>OL</sub>	LOW level output voltage	V <sub>IN</sub> =V <sub>IH</sub>	I <sub>OL</sub> =20μA	2.0			0.1		0.1		0.1	V
				4.5			0.1		0.1		0.1	
				6.0			0.1		0.1		0.1	
		or V <sub>IL</sub>	I <sub>OL</sub> =4mA I <sub>OL</sub> =5.2mA	4.5		0.17	0.26		0.33		0.4	
				6.0		0.15	0.26		0.33		0.4	
I <sub>IN</sub>	Input leakage Current	V <sub>IN</sub> =V <sub>CC</sub> or GND	6.0			0.1		1.0		1.0	μA	
I <sub>CC</sub>	Quiescent Supply Current	V <sub>IN</sub> =V <sub>CC</sub> or GND I <sub>out</sub> =0μA	6.0			2		20		40	μA	

DC Electrical Characteristics for HCT

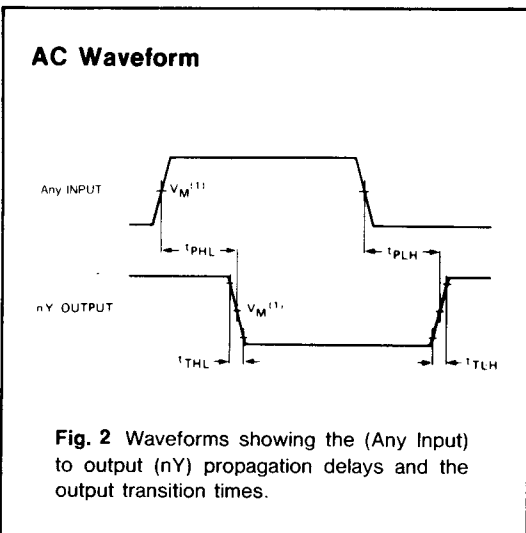
SYMBOL	PARAMETER	TEST CONDITION	V <sub>CC</sub> (V)	T <sub>A</sub> =25°C			GD74HCT58		GD54HCT58		UNIT	
				MIN.	TYP.	MAX.	MIN.	MAX.	MIN.	MAX.		
V <sub>IH</sub>	HIGH level input Voltage		4.5 to 5.5	2.0			2.0		2.0		V	
V <sub>IL</sub>	LOW level input voltage		4.5 to 5.5			0.8		0.8		0.8	V	
V <sub>OH</sub>	HIGH level output voltage	V <sub>IN</sub> =V <sub>IH</sub>	I <sub>OH</sub> =-20μA	4.5	4.4	4.5		4.4		4.4	V	
				4.5	3.98	4.3		3.84		3.7		
		or V <sub>IL</sub>	I <sub>OH</sub> =-4mA	4.5								
				4.5								
V <sub>OL</sub>	LOW level output voltage	V <sub>IN</sub> =V <sub>IH</sub>	I <sub>OL</sub> =20μA	4.5			0.1		0.1		V	
				4.5								
		or V <sub>IL</sub>	I <sub>OL</sub> =4mA	4.5		0.17	0.26		0.33			0.4
				4.5								
I <sub>IN</sub>	Input leakage Current	V <sub>IN</sub> =V <sub>CC</sub> or GND	5.5			0.1		1.0		1.0	μA	
I <sub>CC</sub>	Quiescent Supply Current	V <sub>IN</sub> =V <sub>CC</sub> or GND I <sub>out</sub> =0μA	5.5			2		20		40	μA	

**AC Characteristics for HC:**  $t_r=t_f=6ns$   $C_L=50pF$

SYMBOL	PARAMETER	V <sub>CC</sub> (V)	T <sub>A</sub> =25°C			GD74HC58		GD54HC58		UNIT
			MIN.	TYP.	MAX.	MIN.	MAX.	MIN.	MAX.	
t <sub>PLH</sub> / t <sub>PHL</sub>	Propagation delay time Any Input to nY	2.0		54	125		158		186	ns
		4.5		13	25		32		37	
		6.0		11	21		27		32	
t <sub>TLH</sub> / t <sub>THL</sub>	Output transition time	2.0		28	75		95		110	ns
		4.5		8	15		19		22	
		6.0		7	13		16		19	

**AC Characteristics for HCT:**  $t_r=t_f=6ns$   $C_L=50pF$

SYMBOL	PARAMETER	V <sub>CC</sub> (V)	T <sub>A</sub> =25°C			GD74HCT58		GD54HCT58		UNIT
			MIN.	TYP.	MAX.	MIN.	MAX.	MIN.	MAX.	
t <sub>PLH</sub> / t <sub>PHL</sub>	Propagation delay time Any Input to nY	4.5		17	29		36		41	ns
t <sub>TLH</sub> / t <sub>THL</sub>	Output transition time	4.5		8	15		19		22	ns



**Note to AC waveform**

- (1) HC : V<sub>M</sub>=50%. V<sub>i</sub>=GND to V<sub>CC</sub>
- HCT: V<sub>M</sub>=1.3V. V<sub>i</sub>=GND to 3V.